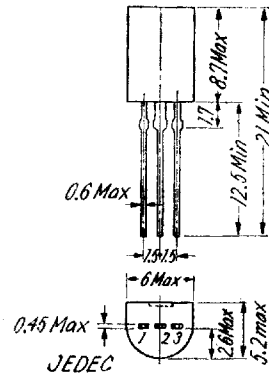


絶対最大定格 Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	2SK79
Drain-to-Gate Voltage	V_{DGO}	120V
Source-to-Gate Voltage	V_{SGO}	10V
Drain Current	I_D	200mA
Gate Current	I_G	20mA
Total Power Dissipation	P_T	750mW
Junction Temperature	T_j	120°C
Storage Temperature	T_{stg}	-50~+150°C

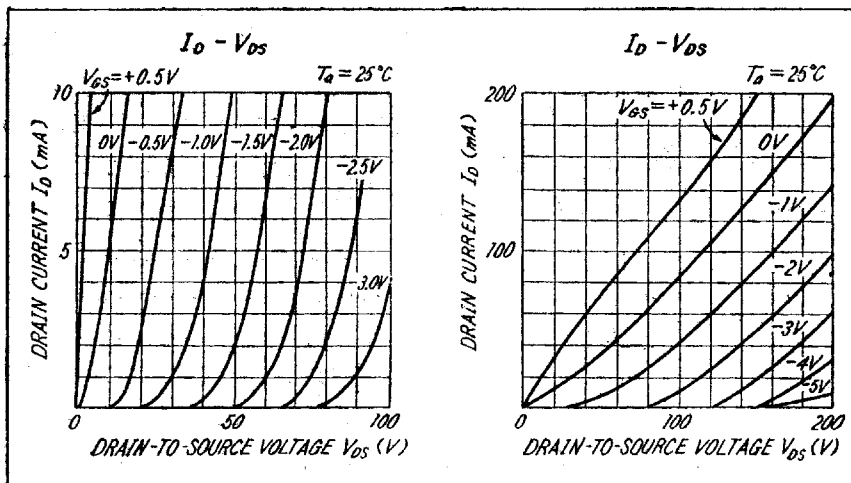


1. Emitter
 2. Base
 3. Collector
- Unit : mm

電気的特性 Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-to-Gate Voltage	V_{DGO}	$I_D = 0.1\text{mA}$	120			V
Source-to-Gate Voltage	V_{SGO}	$I_S = 0.1\text{mA}$	10			V
Drain Cutoff Current	I_{DGO}	$V_{DG} = 50\text{V}, I_S = 0\text{A}$			200	nA
Gate Cutoff Current	I_{GSS}	$V_{GS} = 6\text{V}, V_{DS} = 0\text{A}$			200	nA
Drain-to-Source On-State Voltage	V_{on}	$V_{GS} = 0.3\text{V}, I_D = 7\text{mA}$			10	V
Pinch-off Voltage	V_p	$V_{DS} = 100\text{V}, I_D = 300\mu\text{A}$		-4.5	-9.5	V
Voltage Amplification Ratio	μ	$V_{DS} = 50\text{V}, I_D = 4\text{mA}, f = 1\text{kHz}$	15	30		
Forward Transfer Conductance	g_m	$V_{DS} = 50\text{V}, I_D = 4\text{mA}, f = 1\text{kHz}$		14		m^2S
Input Capacitance	C_{ip}	$V_{DS} = 50\text{V}, I_D = 4\text{mA}, f = 1\text{MHz}$		16		pF
Output Capacitance	C_p	$V_{DS} = 50\text{V}, I_D = 4\text{mA}, f = 1\text{MHz}$		2		k Ω
	C_o			4		pF
Junction-to-Ambient Thermal Resistance	θ_{j-a}				126	$^\circ\text{C/W}$
Noise Figure	NF	$V_{DS} = 50\text{V}, I_D = 4\text{mA}, R_G = 500\text{k}\Omega, f = 10\text{Hz}$			30	dB

[第1表] 2SK79 の最大定格と電気的特性



[第19図] 2SK79 の $I_D - V_{DS}$ 特性